PNP/NPN Epitaxial Planar Silicon Transistors



# 2SB1141/2SD1681

# 18V/1.2A Switching Applications

## **Applications**

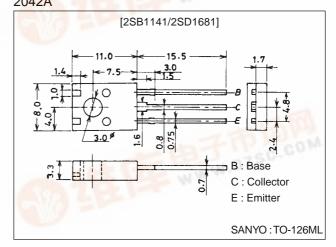
· Converters, relay drivers, low-voltage and high power AF Amplifier.

#### **Features**

- · Low saturation voltage and excellent linearity of hFE.
- · Wide ASO.

# **Package Dimensions**

unit:mm 2042A



(): 2SB1141

# **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit	
Collector-to-Base Voltage	V <sub>CBO</sub>		(-)20	V	
Collector-to-Emitter Voltage	VCEO		(–)18	V	
Emitter-to-Base Voltage	V <sub>EBO</sub>	140	(-)5	V	
Collector Current	I <sub>C</sub>		(-)1.2	Α	
Collector Current (Pulse)	I <sub>CP</sub>	- LA [15]	(-)2.0	А	
Collector Dissipation	PC	AND AND LOSS W	1.5	W	
		Tc=25°C	10	W	
Junction Temperature	Tj		150	°C	
Storage Temperature	Tstg	O Calif	-55 to +125	°C	

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions		Ratings			
Farameter	Symbol	Conditions	min	typ	max	Unit	
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =(-)15V, I <sub>E</sub> =0			(-)100	nA	
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0		1 5	(-)100	nA	
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)100mA	70*		400*	:0 =	
DC Current Gain	h <sub>FE</sub> 2	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)1A	40	W 107			
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)50mA	A A	150		MHz	
Output Capacitance	Coh	V <sub>CB</sub> =(-)10V, f=1MHz		(30)20		pF	

\*: The 2SB1141/2SD1681 are classified by 100mA  $h_{FE}$  as follows:

70 Q 140 100 R 200 140 S 280 200 T		70 Q	140	100	R	200	140	S	280	200	Т	40	0
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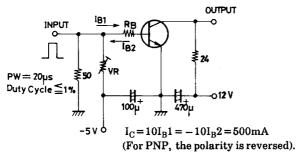
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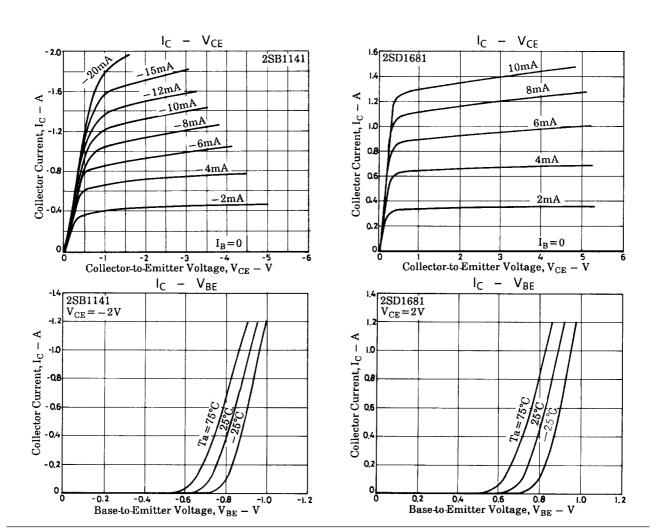
### 2SB1141/2SD1681

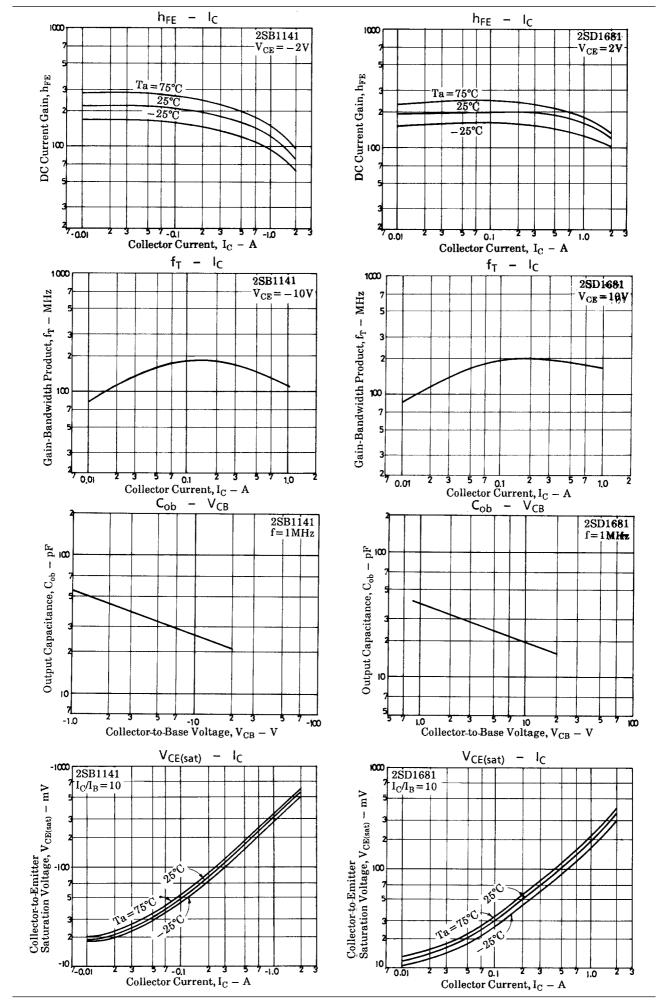
Parameter	Symbol	Conditions		Ratings			
Farameter	Symbol	Conditions	min	typ	max	Unit	
Collector-to-Emitter Saturation Voltage	VCE(sat)	I <sub>C</sub> =(-)500mA, I <sub>B</sub> =(-)50mA		(-170)	(-400)	mV	
				120	300	mV	
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =(-)500mA, I <sub>B</sub> =(-)50mA		(-)0.85	(-)1.2	V	
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =(-)10μΑ, I <sub>E</sub> =0	(–)20			V	
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =(−)1mA, R <sub>BE</sub> =∞	(–)18			V	
Emitter-to-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	$I_{E}=(-)10\mu A, I_{C}=0$	(–)5			V	
Turn-ON Time	ton	See specified Test Circuit		50		ns	
Storage Time	t <sub>stg</sub>	See specified Test Circuit		(60)		ns	
				200		ns	
Fall Time	t <sub>f</sub>	See specified Test Circuit		70		ns	

### **Switching Time Test Circuit**

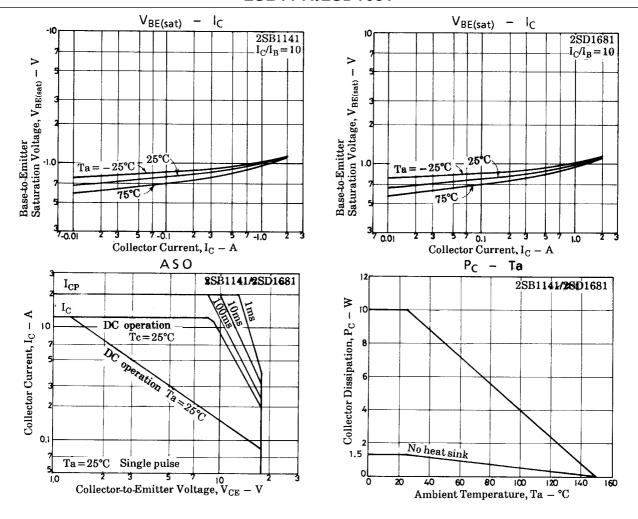


Unit (resistance :  $\Omega$ , capacitance : F)





#### 2SB1141/2SD1681



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